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Acronyms

6T	six transistor
AOI	And/Or/Invert
BL	bitline
BW	Baugh-Wooley
CDF	Cumulative Distribution Function
CE	Constant Electric Field
CMOS	Complementary MOSFET
CV	Constant Voltage
DIBL	Drain-Induced Barrier Lowering
DIO	Data Input/Output
DLMS	Delayed Least Mean Square
DSM	Deep Sub-Micron
DSP	Digital Signal Processor
DVS	Dynamic Voltage Scaling
EDP	energy-delay product
EKV	Enz, Krummenacher, and Vittoz
FBB	Forward Body Bias
FFT	Fast Fourier Transform
FIR	Finite Impulse Response
FO4	Fan-Out of 4
GIDL	Gate-Induced Drain Leakage
IC	Integrated Circuit
ITRS	International Technology Roadmap for Semiconductors
LFSR	Linear Feedback Shift Register
LVD	Local Voltage Dithering
MCU	Microcontroller Units
MTCMOS	multi-threshold CMOS
nMOS	n-type MOSFET
NTRS	National Technology Roadmap for Semiconductors
PDP	power delay product
P-nMOS	Pseudo-NMOS

pMOS	p-type MOSFET
QCV	Quasi-Constant Voltage
RO	ring oscillator
RBB	Reverse Body Bias
RBL	read bitline
RFID	Radio Frequency Identification
RVFFT	Real-Valued FFT
RWL	read wordline
SER	Soft Error Rate
SIA	Semiconductor Industry Association
SNM	Static Noise Margin
SOI	Silicon on Insulator
SRAM	Static Random Access Memory
SS	Strong nMOS, Strong pMOS
SW	Strong nMOS, Weak pMOS
TG	Transmission Gate
TI	Texas Instruments
TT	Typical nMOS, Typical pMOS
UDVS	Ultra-Dynamic Voltage Scaling
ULP	Ultra Low Power
VCO	voltage-controlled oscillator
VLIW	Very-Long Instruction Word
VTC	Voltage Transfer Characteristic
WL	wordline
WS	Weak nMOS, Strong pMOS
WW	Weak nMOS, Weak pMOS

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